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said base layer comprising a SiGeC ternary mixed crystal having a C concentration profile such that a C concentration in said base layer increases from a first interface facing said emitter layer

B1

to a second interface facing said collector layer,

wherein there is formed an interface layer between said base layer and said emitter layer such that said interface layer contains Si and C.

B2

11. (Amended) A heterobipolar transistor as claimed in claim 1, wherein there is formed another interface layer between said base layer and said collector layer such that said another interface layer contains Si and C.

Claims 9 and 10 have been canceled.